aqueous treatment agent solution for oxidizing a polished surface of the semiconductor wafer by action of the aqueous treatment agent solution; and

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the wafer being brought into contact with the aqueous treatment agent solution in a manner which is selected from the group consisting of (a) spraying the semiconductor wafer with the aqueous treatment agent solution, (b) dipping the semiconductor wafer into the aqueous treatment agent solution and (c) applying the aqueous treatment agent solution to the polished surface of the semiconductor wafer by means of a cloth which has been moistened with the aqueous treatment agent solution.

Please cancel claims 3, 4 and 5 without prejudice.

Please amend claims 6, 7, 9, 10, 11 and 13 as follows:

In line 1 of each of claim 6, claim 7, claim 9, claim 10 and claim 13, please cancel "Claim 1" and please insert --Claim 14-- therefore.

In claim 11, in line 1, please cancel "Claim 2" and please insert -- Claim 14-- therefor.

Please add new claim 15 which is based upon original claim 8 as follows: